

DLP5500 DLP® 0.55 XGA 系列 450 DMD

1 特性

- 0.55 英寸微镜阵列对角线
 - 1024 × 768 铝阵列，微米级微镜（XGA 分辨率）
 - 10.8μm 微镜间距
 - ±12°微镜倾斜角（相对于平板状态）
 - 设计用于边缘照明
- 设计用于宽带可见光（420nm 至 700nm）：
 - 窗口传输 97%（单通、通过双窗面）
 - 微镜反射率 88%
 - 阵列衍射效率 86%
 - 阵列填充因子 92%
- 16 位低压差分信令 (LVDS)、双倍数据速率 (DDR) 输入数据总线
- 200MHz 输入数据时钟速率
- 针对高速图形速率的专用 DLPC200 控制器
 - 5,000Hz（1 位二进制图形）
 - 500Hz（8 位灰度图形）
- 450 系列封装特性：
 - 散热区域 18mm × 12mm，支持高屏幕流明 (>2000 lm)
 - 149 微针栅阵列可靠电气连接
 - 封装匹配 Amphenol InterCon 系统 450-2.700-L-13.25-149 插孔

2 应用

- 工业
 - 针对机器视觉和质量控制的 3D 扫描仪
 - 3D 打印
 - 直接成像平版印刷
 - 激光打标和修复
 - 工业和医疗成像
 - 医疗仪器
 - 数字曝光系统
- 医疗
 - 眼科
 - 针对四肢和皮肤测量的 3D 扫描仪
 - 高光谱成像
- 显示屏
 - 3D 成像显微镜
 - 智能和自适应照明

3 说明

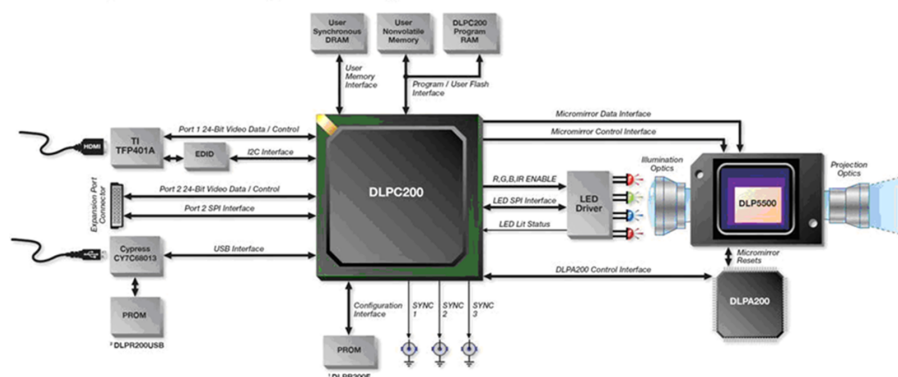
拥有超过 750000 个微镜的高分辨率 DLP5500 (0.55" XGA) 数字微镜器件 (DMD) 是一种空间光调制器 (SLM)，调制入射光的振幅、方向和/或相位。这种高级照明控制技术 适用于 工业、医疗和消费品市场中的许多应用。DLP5500 在 3D 打印 应用中提供高分辨率。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
DLP5500	CPGA (149)	22.30mm × 32.20mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

4 典型应用原理图



目录

1	特性	1	9.2	Functional Block Diagram	20
2	应用	1	9.3	Feature Description	21
3	说明	1	9.4	Device Functional Modes	24
4	典型应用原理图	1	9.5	Window Characteristics and Optics	24
5	修订历史记录	2	9.6	Micromirror Array Temperature Calculation	25
6	说明 (续)	4	9.7	Micromirror Landed-on/Landed-Off Duty Cycle	27
7	Pin Configuration and Functions	4	10	Application and Implementation	29
8	Specifications	7	10.1	Application Information	29
8.1	Absolute Maximum Ratings	7	10.2	Typical Application	30
8.2	Storage Conditions	7	11	Power Supply Recommendations	32
8.3	ESD Ratings	7	11.1	DMD Power-Up and Power-Down Procedures	32
8.4	Recommended Operating Conditions	8	12	Layout	32
8.5	Thermal Information	10	12.1	Layout Guidelines	32
8.6	Electrical Characteristics	10	12.2	Layout Example	33
8.7	Timing Requirements	11	13	器件和文档支持	34
8.8	System Mounting Interface Loads	15	13.1	器件支持	34
8.9	Micromirror Array Physical Characteristics	16	13.2	文档支持	34
8.10	Micromirror Array Optical Characteristics	17	13.3	相关文档	34
8.11	Window Characteristics	18	13.4	社区资源	34
8.12	Chipset Component Usage Specification	18	13.5	商标	35
9	Detailed Description	19	13.6	静电放电警告	35
9.1	Overview	19	13.7	术语表	35
			14	机械、封装和可订购信息	35

5 修订历史记录

Changes from Revision F (May 2015) to Revision G	Page
• 已更改 图 19 的 DMD 标记图像对象	34

Changes from Revision E (September 2013) to Revision F	Page
• 已添加 ESD 额定值, 特性 说明 部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分	1
• Changed Incorrect V_{CC2} value from 9V to 8V	7
• Changed LVDS f_{clock} to 200 MHz - previously incorrectly listed as 150 MHz	9
• Added Max Recommended DMD Temperature – Derating Curve	9
• Added LVCMOS Output Measurement Condition Figure	10
• Changed Incorrect t_c value from 4 ns to 5 ns (200 MHz clock)	11
• Changed Incorrect t_w value from 1.25 ns to 2.5 ns (200 MHz clock)	11
• Changed SCP Bus Diagrams	11
• Added LVDS Voltage Definition Figure	12
• Changed LVDS Waveform Requirements Figure	13
• Added LVDS Equivalent Input Circuit Figure	13
• Added LVDS & SCP Rise and Fall Time Figures	14
• Moved the <i>Mechanical</i> section from <i>Recommended Operating Conditions</i> table to the <i>System Mounting Interface Loads</i> section	15
• Added <i>Micromirror Array Physical Characteristics</i> section	16
• Changed Micromirror Array Physical Characteristics Figure to generic image (M x N)	16
• Added <i>Micromirror Array Optical Characteristics</i> section	17

• Changed specular reflectivity wavelength range to 420 - 700 nm (from 400 - 700 nm) to match Recommended Operating Conditions	17
• Changed Micromirror Landed Orientation and Tilt Figure to generic image (M x N)	18
• Added <i>Window Characteristics</i> section	18
• Added <i>Chipset Component Usage Specification</i> section	18
• Changed Micromirror Array, Pitch, Hinge Axis Orientation Figure to generic image (M x N)	22
• Changed Micromirror States: On, Off, Flat Figure to generic DMD image	23
• Changed Test Point locations from TC1 & TC2 to TP1 - TP5	25
• Changed Test Point location Diagram to show TP1 - TP5.....	26
• Added <i>Micromirror Landed-on/Landed-Off Duty Cycle</i> section	27
• Changed Typical Application diagram	30
• Replaced "DAD" with "DLPA200"	31

Changes from Revision D (October 2012) to Revision E	Page
• 删除了“器件型号命名规则”部分	34

Changes from Revision C (June 2012) to Revision D	Page
• 将器件型号命名规则从“DLP5500FYA”更改为“DLP5500AFYA”	34
• 将“机械 ICD”更新至 V2，窗口高度略有更改	34

Changes from Revision B (September 2011) to Revision C	Page
• 将“封装尺寸和插座”信息添加至 特性 列表	1
• 已删除 “说明”部分的 冗余信息	1
• Changed the Illumination power density Max value of <420 mm From: 20 To: 2 mW/cm ²	7
• Changed Storage temperature range and humidity values in Absolute Maximum Ratings	7
• Added Operating Case Temperature, Operating Humidity, Operating Device Temperature Gradient and Operating Landed Duty-Cycle to RECOMMENDED OPERATING CONDITIONS.	8
• Added Mirror metal specular reflectivity and Illumination overfill values to "Micromirror Array Optical Characteristics" table	17
• Corrected the C _{L2W} , Q _{array} and T _{array} values in Micromirror Array Temperature Calculation for Uniform Illumination.	26
• 更正了相关文档中的文献编号	34

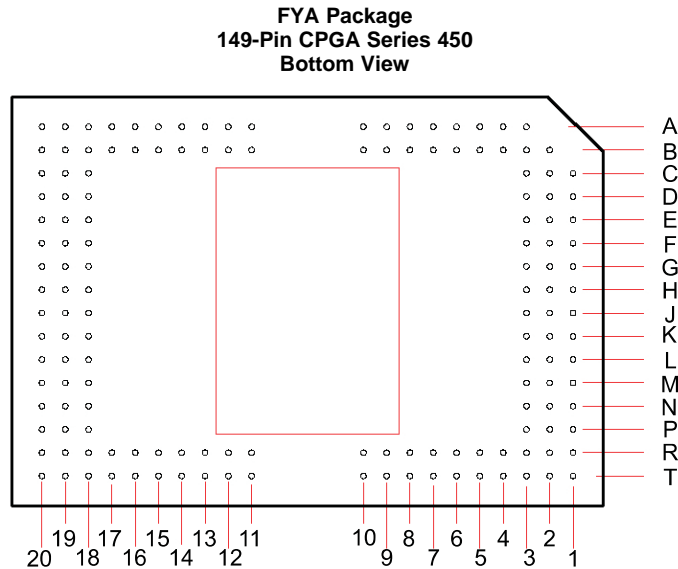
Changes from Revision A (June 2010) to Revision B	Page
• Changed the window refractive index NOM spec From: 1.5090 To: 1.5119	17
• Added table note "At a wavelength of 632.8 nm"	17

Changes from Original (April 2010) to Revision A	Page
• Changed V _{REF} to V _{CC1}	7
• Added V _{ID} to the absolute max table	7
• Added V _{MBRST} to the absolute max table	7
• Clarified Note6 measurement point	7
• Changed the Illumination power density Max value of <420 mm From: 2 To: 20 mW/cm ²	7
• 已添加 更多相关文档	34

6 说明（续）

XGA 分辨率支持扫描更大的物体，这对于 3D 机器视觉 应用有直接帮助。DLP5500 需要与 DLPC200 数字控制器和 DLPA200 模拟驱动器结合使用才能实现可靠功能和操作。这种专用芯片组提供可靠的高分辨率 XGA 和高速系统解决方案。

7 Pin Configuration and Functions



Pin Functions

PIN ⁽¹⁾		TYPE (I/O/P)	SIGNAL	DATA RATE ⁽²⁾	INTERNAL TERM ⁽³⁾	CLOCK	DESCRIPTION	TRACE (mils) ⁽⁴⁾
NAME	NO.							
DATA INPUTS								
D_AN1	G20	Input	LVC MOS	DDR	Differential	DCLK_A	Input data bus A (LVDS)	715
D_AP1	H20	Input	LVC MOS	DDR	Differential	DCLK_A		744
D_AN3	H19	Input	LVC MOS	DDR	Differential	DCLK_A		688
D_AP3	G19	Input	LVC MOS	DDR	Differential	DCLK_A		703
D_AN5	F18	Input	LVC MOS	DDR	Differential	DCLK_A		686
D_AP5	G18	Input	LVC MOS	DDR	Differential	DCLK_A		714
D_AN7	E18	Input	LVC MOS	DDR	Differential	DCLK_A		689
D_AP7	D18	Input	LVC MOS	DDR	Differential	DCLK_A		705
D_AN9	C20	Input	LVC MOS	DDR	Differential	DCLK_A		687
D_AP9	D20	Input	LVC MOS	DDR	Differential	DCLK_A		715
D_AN11	B18	Input	LVC MOS	DDR	Differential	DCLK_A		715
D_AP11	A18	Input	LVC MOS	DDR	Differential	DCLK_A		732
D_AN13	A20	Input	LVC MOS	DDR	Differential	DCLK_A		686
D_AP13	B20	Input	LVC MOS	DDR	Differential	DCLK_A		715
D_AN15	B19	Input	LVC MOS	DDR	Differential	DCLK_A		700
D_AP15	A19	Input	LVC MOS	DDR	Differential	DCLK_A		719

(1) The following power supplies are required to operate the DMD: VCC, VCCI, VCC2. VSS must also be connected.

(2) DDR = Double Data Rate. SDR = Single Data Rate. Refer to the [Timing Requirements](#) for specifications and relationships.

(3) Refer to [Electrical Characteristics](#) for differential termination specification.

(4) Internal Trace Length (mils) refers to the Package electrical trace length. See the *DLP® 0.55 XGA Chip-Set Data Manual (DLPZ004)* for details regarding signal integrity considerations for end-equipment designs.

Pin Functions (continued)

PIN ⁽¹⁾		TYPE (I/O/P)	SIGNAL	DATA RATE ⁽²⁾	INTERNAL TERM ⁽³⁾	CLOCK	DESCRIPTION	TRACE (mils) ⁽⁴⁾
NAME	NO.							
D_BN1	K20	Input	LVCMOS	DDR	Differential	DCLK_B	Input data bus B (LVDS)	716
D_BP1	J20	Input	LVCMOS	DDR	Differential	DCLK_B		745
D_BN3	J19	Input	LVCMOS	DDR	Differential	DCLK_B		686
D_BP3	K19	Input	LVCMOS	DDR	Differential	DCLK_B		703
D_BN5	L18	Input	LVCMOS	DDR	Differential	DCLK_B		686
D_BP5	K18	Input	LVCMOS	DDR	Differential	DCLK_B		714
D_BN7	M18	Input	LVCMOS	DDR	Differential	DCLK_B		693
D_BP7	N18	Input	LVCMOS	DDR	Differential	DCLK_B		709
D_BN9	P20	Input	LVCMOS	DDR	Differential	DCLK_B		687
D_BP9	N20	Input	LVCMOS	DDR	Differential	DCLK_B		715
D_BN11	R18	Input	LVCMOS	DDR	Differential	DCLK_B		702
D_BP11	T18	Input	LVCMOS	DDR	Differential	DCLK_B		719
D_BN13	T20	Input	LVCMOS	DDR	Differential	DCLK_B		686
D_BP13	R20	Input	LVCMOS	DDR	Differential	DCLK_B		715
D_BN15	R19	Input	LVCMOS	DDR	Differential	DCLK_B		680
D_BP15	T19	Input	LVCMOS	DDR	Differential	DCLK_B		700
DCLK_AN	D19	Input	LVCMOS	-	Differential	—	Input data bus A Clock (LVDS)	700
DCLK_AP	E19	Input	LVCMOS	-	Differential	—		728
DCLK_BN	N19	Input	LVCMOS	-	Differential	—	Input data bus B Clock (LVDS)	700
DCLK_BP	M19	Input	LVCMOS	-	Differential	—		728
DATA CONTROL INPUTS								
SCTRL_AN	F20	Input	LVCMOS	DDR	Differential	DCLK_A	Data Control (LVDS)	716
SCTRL_AP	E20	Input	LVCMOS	DDR	Differential	DCLK_A		731
SCTRL_BN	L20	Input	LVCMOS	DDR	Differential	DCLK_B		707
SCTRL_BP	M20	Input	LVCMOS	DDR	Differential	DCLK_B		722
SERIAL COMMUNICATION (SCP) AND CONFIGURATION								
SCP_CLK	A8	Input	LVCMOS	—	Pull-Down	—		—
SCP_DO	A9	Output	LVCMOS	—	—	SCP_CLK		—
SCP_DI	A5	Input	LVCMOS	—	Pull-Down	SCP_CLK		—
SCP_EN	B7	Input	LVCMOS	—	Pull-Down	SCP_CLK		—
PWRDN	B9	Input	LVCMOS	—	Pull-Down	—		—
MICROMIRROR BIAS CLOCKING PULSE								
MODE_A	A4	Input	LVCMOS	—	Pull-Down	—		—
MBRST0	C3	Input	Analog	—	—	—	Micromirror Bias Clocking Pulse "MBRST" signals "clock" micromirrors into state of LVCMOS memory cell associated with each mirror.	—
MBRST1	D2	Input	Analog	—	—	—		—
MBRST2	D3	Input	Analog	—	—	—		—
MBRST3	E2	Input	Analog	—	—	—		—
MBRST4	G3	Input	Analog	—	—	—		—
MBRST5	E1	Input	Analog	—	—	—		—
MBRST6	G2	Input	Analog	—	—	—		—
MBRST7	G1	Input	Analog	—	—	—		—
MBRST8	N3	Input	Analog	—	—	—		—
MBRST9	M2	Input	Analog	—	—	—		—
MBRST10	M3	Input	Analog	—	—	—		—
MBRST11	L2	Input	Analog	—	—	—		—
MBRST12	J3	Input	Analog	—	—	—		—
MBRST13	L1	Input	Analog	—	—	—		—
MBRST14	J2	Input	Analog	—	—	—		—
MBRST15	J1	Input	Analog	—	—	—	—	

Pin Functions (continued)

PIN ⁽¹⁾		TYPE (I/O/P)	SIGNAL	DATA RATE ⁽²⁾	INTERNAL TERM ⁽³⁾	CLOCK	DESCRIPTION	TRACE (mils) ⁽⁴⁾
NAME	NO.							
POWER								
V _{CC}	B11,B12,B13,B16,R12,R13,R16,R17	Power	Analog	—	—	—	Power for LVCMOS Logic	—
V _{CCI}	A12,A14,A16,T12,T14,T16	Power	Analog	—	—	—	Power supply for LVDS Interface	—
V _{CC2}	C1,D1,M1,N1	Power	Analog	—	—	—	Power for High Voltage CMOS Logic	—
V _{SS}	A6,A11,A13,A15,A17,B4,B5,B8,B14,B15,B17,C2,C18,C19,F1,F2,F19,H1,H2,H3,H18,J18,K1,K2,L19,N2,P18,P19,R4,R9,R14,R15,T7,T13,T15,T17	Power	Analog	—	—	—	Common return for all power inputs	—
RESERVED SIGNALS (Not for use in system)								
RESERVED_R7	R7	Input	LVC MOS	—	Pull-Down	—	Pins should be connected to V _{SS}	—
RESERVED_R8	R8	Input	LVC MOS	—	Pull-Down	—		—
RESERVED_T8	T8	Input	LVC MOS	—	Pull-Down	—		—
RESERVED_B6	B6	Input	LVC MOS	—	Pull-Down	—		—
NO_CONNECT	A3, A7, A10, B2, B3, B10, E3, F3, K3, L3, P1, P2, P3, R1, R2, R3, R5, R6, R10, R11, T1, T2, T3, T4, T5, T6, T9, T10, T11	—	—	—	—	—	DO NOT CONNECT	—

8 Specifications

8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
ELECTRICAL				
V _{CC}	Voltage applied to V _{CC} ⁽²⁾⁽³⁾	–0.5	4	V
V _{CCI}	Voltage applied to V _{CCI} ⁽²⁾⁽³⁾	–0.5	4	V
	Delta supply voltage V _{CC} – V _{CCI} ⁽⁴⁾		0.3	V
V _{ID}	Maximum differential voltage, Damage can occur to internal resistor if exceeded, See Figure 6		700	mV
V _{CC2}	Voltage applied to V _{OFFSET} ⁽²⁾⁽³⁾⁽⁴⁾	–0.5	8	V
V _{MBRST}	Voltage applied to MBRST[0:15] Input Pins	–28	28	V
	Voltage applied to all other pins ⁽²⁾	–0.5	V _{CC} + 0.3	V
I _{OH}	Current required from a high-level output V _{OH} = 2.4 V		–20	mA
I _{OL}	Current required from a low-level output V _{OL} = 0.4 V		15	mA
ENVIRONMENTAL				
T _{CASE}	Case temperature: operational ^{(5) (6)}	–20	90	°C
	Case temperature: non-operational ⁽⁶⁾	–40	90	°C
	Dew Point (Operating and non-Operating)		81	°C

- (1) Stresses beyond those listed under [Absolute Maximum Ratings](#) may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under [Recommended Operating Conditions](#). Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages referenced to V_{SS} (ground).
- (3) Voltages V_{CC}, V_{CCI}, and V_{CC2} are required for proper DMD operation.
- (4) Exceeding the recommended allowable absolute voltage difference between V_{CC} and V_{CCI} may result in excess current draw. The difference between V_{CC} and V_{CCI}, |V_{CC} – V_{CCI}|, should be less than .3V.
- (5) Exposure of the DMD simultaneously to any combination of the maximum operating conditions for case temperature, differential temperature, or illumination power density (see [Recommended Operating Conditions](#)).
- (6) DMD Temperature is the worst-case of any test point shown in [Figure 16](#), or the active array as calculated by the [Micromirror Array Temperature Calculation](#).

8.2 Storage Conditions

applicable before the DMD is installed in the final product

		MIN	MAX	UNIT
T _{stg}	DMD storage temperature	–40	80	°C
T _{DP}	Storage dew point	Storage Dew Point - long-term ⁽¹⁾		24
		Storage Dew Point - short-term ⁽²⁾		28

- (1) Long-term is defined as the usable life of the device.
- (2) Dew points beyond the specified long-term dew point are for short-term conditions only, where short-term is defined as less than 60 cumulative days over the usable life of the device (operating, non-operating, or storage).

8.3 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Electrostatic discharge immunity for LVCMOS [I/O] pins ⁽¹⁾	±2000
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all other pins [power, control pins] except MBRST ⁽²⁾	±2000
		Electrostatic discharge immunity for MBRST[0:15] pins ⁽¹⁾	<250

- (1) Tested in accordance with JESD22-A114-B Electrostatic Discharge (ESD) sensitivity testing Human Body Model (HBM).
- (2) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

8.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
SUPPLY VOLTAGES^{(1) (2)}					
V _{CC}	Supply voltage for LVCMOS core logic	3.15	3.3	3.45	V
V _{CCI}	Supply voltage for LVDS receivers	3.15	3.3	3.45	V
V _{CC2}	Mirror electrode and HVCMOS supply voltage	8.25	8.5	8.75	V
V _{CCI} –V _{CC}	Supply voltage delta (absolute value) ⁽³⁾			0.3	V
V _{MBRST}	Micromirror clocking pulse voltages	–27		26.5	V
LVCMOS PINS					
V _{IH}	High level Input voltage ⁽⁴⁾	1.7	2.5	V _{CC} + 0.15	V
V _{IL}	Low level Input voltage ⁽⁴⁾	–0.3		0.7	V
I _{OH}	High level output current at V _{OH} = 2.4 V			–20	mA
I _{OL}	Low level output current at V _{OL} = 0.4 V			15	mA
T _{PWRDNZ}	PWRDNZ pulse width ⁽⁵⁾	10			ns
SCP INTERFACE					
f _{clock}	SCP clock frequency ⁽⁶⁾			500	kHz
t _{SCP_SKEW}	Time between valid SCPDI and rising edge of SCPCLK ⁽⁷⁾	–800		800	ns
t _{SCP_DELAY}	Time between valid SCPDO and rising edge of SCPCLK ⁽⁷⁾			700	ns
t _{SCP_BYTE_INTERVAL}	Time between consecutive bytes	1			μs
t _{SCP_NEG_ENZ}	Time between falling edge of SCPENZ and the first rising edge of SCPCLK	30			ns
t _{SCP_PW_ENZ}	SCPENZ inactive pulse width (high level)	1			μs
t _{SCP_OUT_EN}	Time required for SCP output buffer to recover after SCPENZ (from tri-state)			1.5	ns
f _{clock}	SCP circuit clock oscillator frequency ⁽⁸⁾	9.6		11.1	MHz

(1) Supply voltages V_{CC}, V_{CCI}, V_{OFFSET}, V_{BIAS}, and V_{RESET} are all required for proper DMD operation. V_{SS} must also be connected.

(2) V_{OFFSET} supply transients must fall within specified max voltages.

(3) To prevent excess current, the supply voltage delta |V_{CCI} – V_{CC}| must be less than specified limit.

(4) Tester Conditions for V_{IH} and V_{IL}:

Frequency = 60MHz. Maximum Rise Time = 2.5 ns at (20% to 80%)

Frequency = 60MHz. Maximum Fall Time = 2.5 ns at (80% to 20%)

(5) PWRDNZ input pin resets the SCP and disables the LVDS receivers. PWRDNZ input pin overrides SCPENZ input pin and tri-states the SCPDO output pin.

(6) The SCP clock is a gated clock. Duty cycle shall be 50% ± 10%. SCP parameter is related to the frequency of DCLK.

(7) Refer to [Figure 3](#).

(8) SCP internal oscillator is specified to operate all SCP registers. For all SCP operations, DCLK is required.

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
LVDS INTERFACE					
f_{clock}	Clock frequency for LVDS interface, DCLK (all channels)		200		MHz
$ V_{\text{ID}} $	Input differential voltage (absolute value) ⁽⁹⁾	100	400	600	mV
V_{CM}	Common mode ⁽⁹⁾		1200		mV
V_{LVDS}	LVDS voltage ⁽⁹⁾	0		2000	mV
$t_{\text{LVDS_RSTZ}}$	Time required for LVDS receivers to recover from PWRDNZ			10	ns
Z_{IN}	Internal differential termination resistance	95		105	Ω
Z_{LINE}	Line differential impedance (PWB/trace)	90	100	110	Ω
ENVIRONMENTAL ⁽¹⁰⁾					
T_{DMD}	Long-term DMD temperature (operational) ^{(11) (12) (13)}	10		40 to 70 ⁽¹²⁾	°C
	Short-term DMD temperature (operational) ^{(11) (14)}	–20		75	°C
T_{WINDOW}	Window temperature – operational ⁽¹⁵⁾			90	°C
$T_{\text{CERAMIC-WINDOW-DELTA}}$	Delta ceramic-to-window temperature -operational ^{(15) (16)}			30	°C
	Long-term dew point (operational & non-operational)			24	°C
	Short-term dew point ^{(13) (17)} (operational & non-operational)			28	°C
ILL_{UV}	Illumination, wavelength < 420 nm			0.68	mW/cm ²
ILL_{VIS}	Illumination, wavelengths between 420 and 700 nm			Thermally Limited ⁽¹⁸⁾	mW/cm ²
ILL_{IR}	Illumination, wavelength > 700 nm			10	mW/cm ²

(9) Refer to [Figure 5](#), [Figure 6](#), and [Figure 7](#).

(10) Optimal, long-term performance and optical efficiency of the Digital Micromirror Device (DMD) can be affected by various application parameters, including illumination spectrum, illumination power density, micromirror landed duty-cycle, ambient temperature (storage and operating), DMD temperature, ambient humidity (storage and operating), and power on or off duty cycle. TI recommends that application-specific effects be considered as early as possible in the design cycle.

(11) DMD Temperature is the worst-case of any thermal test point in [Figure 16](#), or the active array as calculated by the [Micromirror Array Temperature Calculation for Uniform Illumination](#).

(12) Per [Figure 1](#), the maximum operational case temperature should be derated based on the micromirror landed duty cycle that the DMD experiences in the end application. Refer to [Micromirror Landed-on/Landed-Off Duty Cycle](#) for a definition of micromirror landed duty cycle.

(13) Long-term is defined as the average over the usable life of the device.

(14) Short-term is defined as less than 60 cumulative days over the over the usable life of the device.

(15) Window temperature as measured at thermal test points TP2, TP3, TP4 and TP5 in [Figure 16](#). The locations of thermal test points TP2, TP3, TP4 and TP5 in [Figure 16](#) are intended to measure the highest window edge temperature. If a particular application causes another point on the window edge to be at a higher temperature, a test point should be added to that location.

(16) Ceramic package temperature as measured at test point 1 (TP 1) in [Figure 16](#).

(17) Dew points beyond the specified long-term dew point (operating, non-operating, or storage) are for short-term conditions only, where short-term is defined as < 60 cumulative days over the usable life of the device.

(18) Refer to [Thermal Information](#) and [Micromirror Array Temperature Calculation](#).

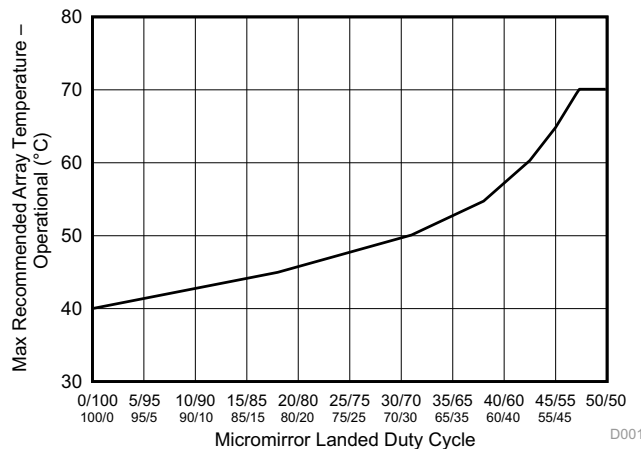


Figure 1. Max Recommended DMD Temperature – Derating Curve

8.5 Thermal Information

THERMAL METRIC	DLP5500	UNIT
	FYA (CPGA)	
	149 PINS	
Thermal resistance from active array to specified point on case (TP1) ⁽¹⁾	0.6	°C/W

(1) For more information, see [Micromirror Array Temperature Calculation](#).

8.6 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OH}	High-level output voltage ⁽¹⁾ , See Figure 2 V _{CC} = 3.0 V, I _{OH} = –20 mA	2.4			V
V _{OL}	Low-level output voltage ⁽¹⁾ , See Figure 2 V _{CC} = 3.6 V, I _{OL} = 15 mA			0.4	V
I _{OZ}	High impedance output current ⁽¹⁾ V _{CC} = 3.6 V			10	μA
I _{IL}	Low-level input current ⁽¹⁾ V _{CC} = 3.6 V, V _I = 0 V			–60	μA
I _{IH}	High-level input current ⁽¹⁾ V _{CC} = 3.6 V, V _I = V _{CC}			200	μA
I _{CC}	Current into V _{CC} pin V _{CC} = 3.6 V,			750	mA
I _{CCI}	Current into V _{OFFSET} pin ⁽²⁾ V _{CCI} = 3.6 V			450	mA
I _{CC2}	Current into V _{CC2} pin V _{CC2} = 8.75V			25	mA
Z _{IN}	Internal Differential Impedance	95		105	Ω
Z _{LINE}	Line Differential Impedance (PWB or Trace)	90	100	110	Ω
C _I	Input capacitance ⁽¹⁾ f = 1 MHz			10	pF
C _O	Output capacitance ⁽¹⁾ f = 1 MHz			10	pF
C _{IM}	Input capacitance for MBRST[0:15] pins f = 1 MHz	160		210	pF

(1) Applies to LVCMOS pins only

(2) Exceeding the maximum allowable absolute voltage difference between V_{CC} and V_{CCI} may result in excess current draw. (Refer to [Absolute Maximum Ratings](#) for details)

LOAD CIRCUIT

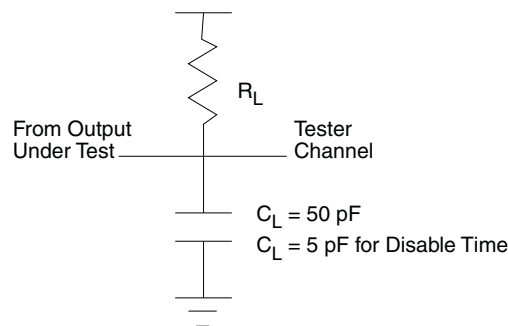


Figure 2. Measurement Condition for LVCMOS Output

8.7 Timing Requirements

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
LVDS TIMING PARAMETERS (See Figure 9)					
t_c	Clock Cycle DCLK_A or DCLK_B		5		ns
t_w	Pulse Width DCLK_A or DCLK_B		2.5		ns
t_s	Setup Time, D_A[0:15] before DCLK_A	.35			ns
t_s	Setup Time, D_B[0:15] before DCLK_B	.35			ns
t_h	Hold Time, D_A[0:15] after DCLK_A	.35			ns
t_h	Hold Time, D_B[0:15] after DCLK_B	.35			ns
t_{skew}	Channel B relative to Channel A	–1.25		1.25	ns
LVDS WAVEFORM REQUIREMENTS (See Figure 6)					
$ V_{ID} $	Input Differential Voltage (absolute difference)	100	400	600	mV
V_{CM}	Common Mode Voltage		1200		mV
V_{LVDS}	LVDS Voltage	0		2000	mV
t_r	Rise Time (20% to 80%)	100		400	ps
t_f	Fall Time (80% to 20%)	100		400	ps
SERIAL CONTROL BUS TIMING PARAMETERS (See Figure 3 and Figure 4)					
f_{SCP_CLK}	SCP Clock Frequency	50		500	kHz
t_{SCP_SKEW}	Time between valid SCP_DI and rising edge of SCP_CLK	–300		300	ns
t_{SCP_DELAY}	Time between valid SCP_DO and rising edge of SCP_CLK			2600	ns
t_{SCP_EN}	Time between falling edge of $\overline{SCP_EN}$ and the first rising edge of SCP_CLK	30			ns
t_{r_SCP}	Rise time for SCP signals			200	ns
t_{fP}	Fall time for SCP signals			200	ns

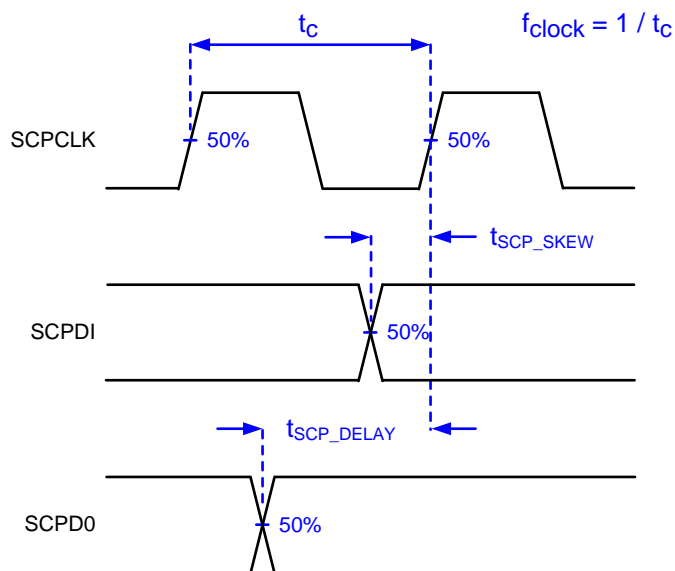


Figure 3. Serial Communications Bus Timing Parameters

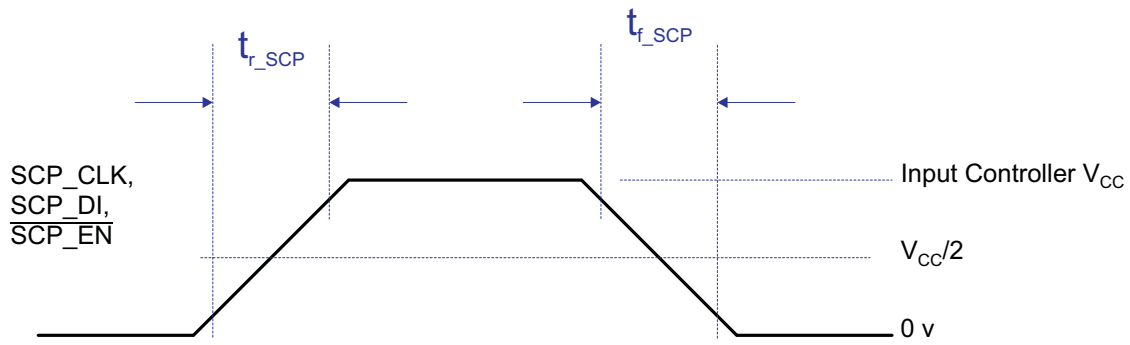
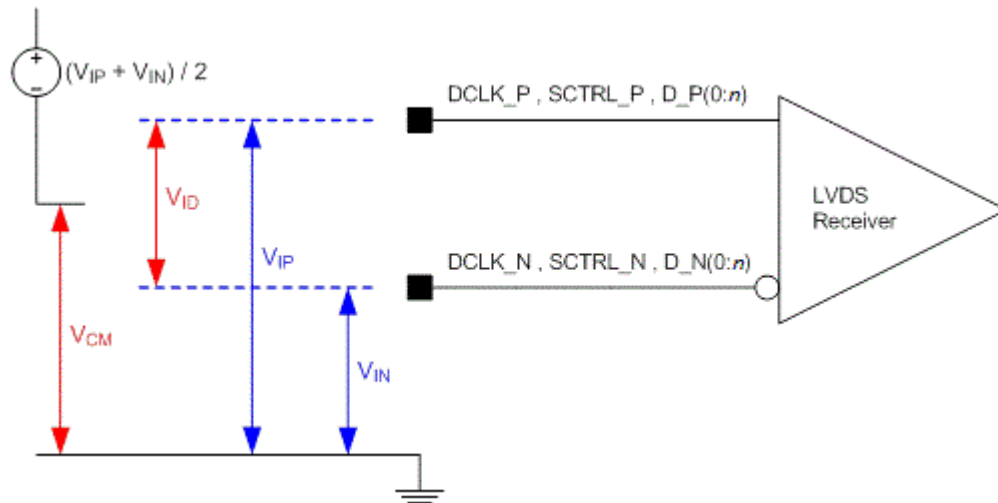


Figure 4. Serial Communications Bus Waveform Requirements



Refer to LVDS Interface section of the [Recommended Operating Conditions](#).

Refer to Pin Configuration and Functions for list of LVDS pins.

Figure 5. LVDS Voltage Definitions (References)

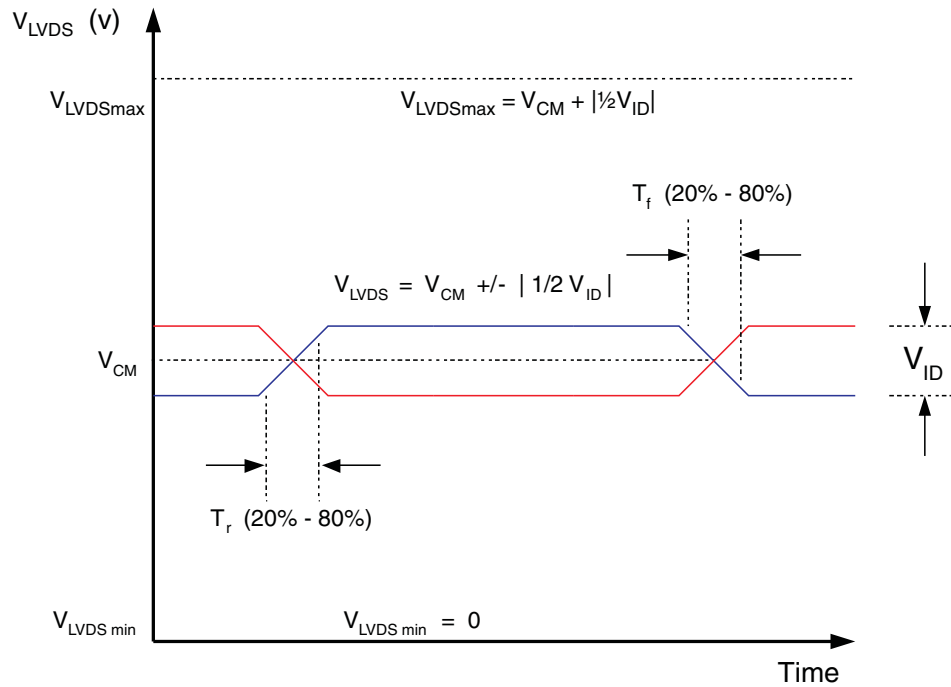


Figure 6. LVDS Waveform Requirements

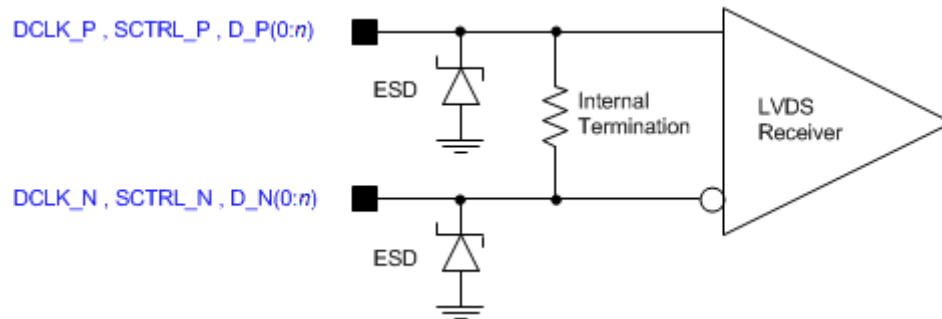
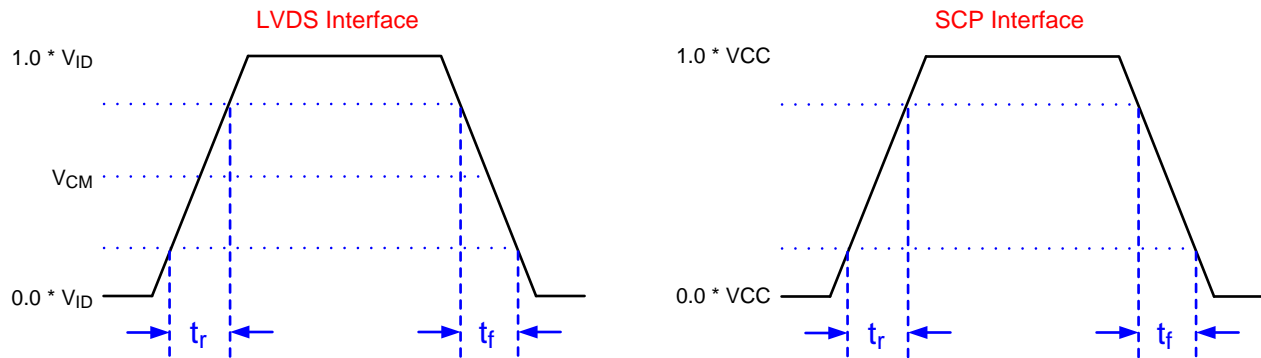


Figure 7. LVDS Equivalent Input Circuit



Not to scale.

Refer to the [Timing Requirements](#).

Refer to [Pin Configuration and Functions](#) for list of LVDS pins and SCP pins.

Figure 8. Rise Time and Fall Time

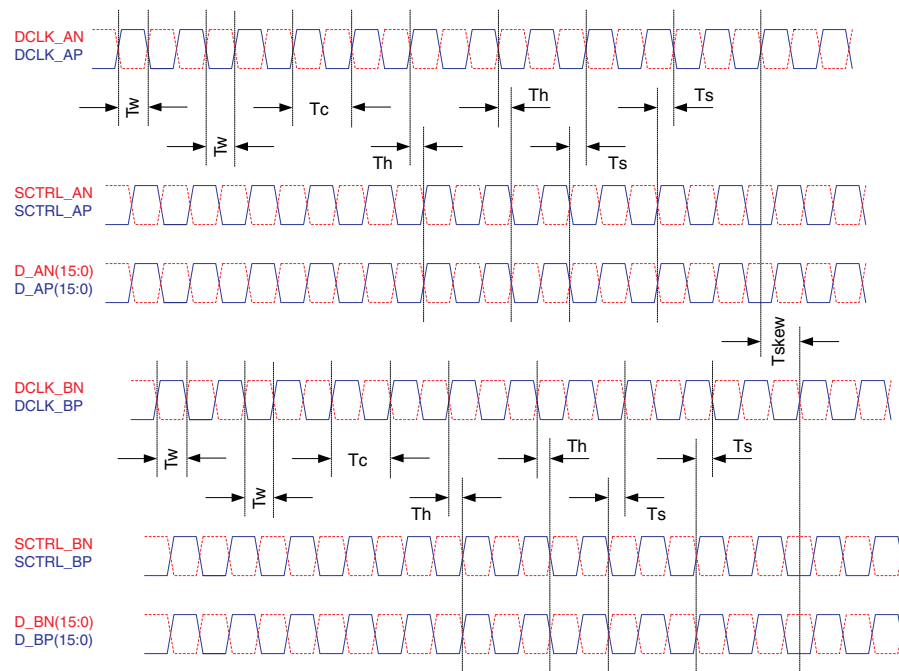


Figure 9. LVDS Timing Waveforms

8.8 System Mounting Interface Loads

PARAMETER			MIN	NOM	MAX	UNIT
Maximum system mounting interface load to be applied to the:	Thermal Interface area	Static load applied to the thermal interface area, See Figure 10			111	N
	Electrical Interface area	Static load applied to each electrical interface area no. 1 and no. 2, See Figure 10			55	N

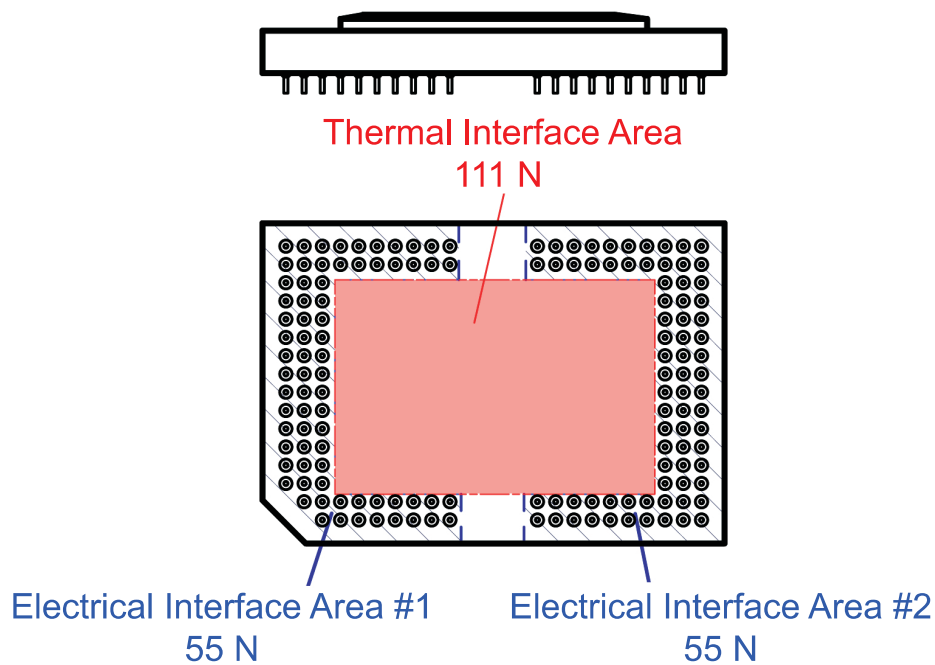


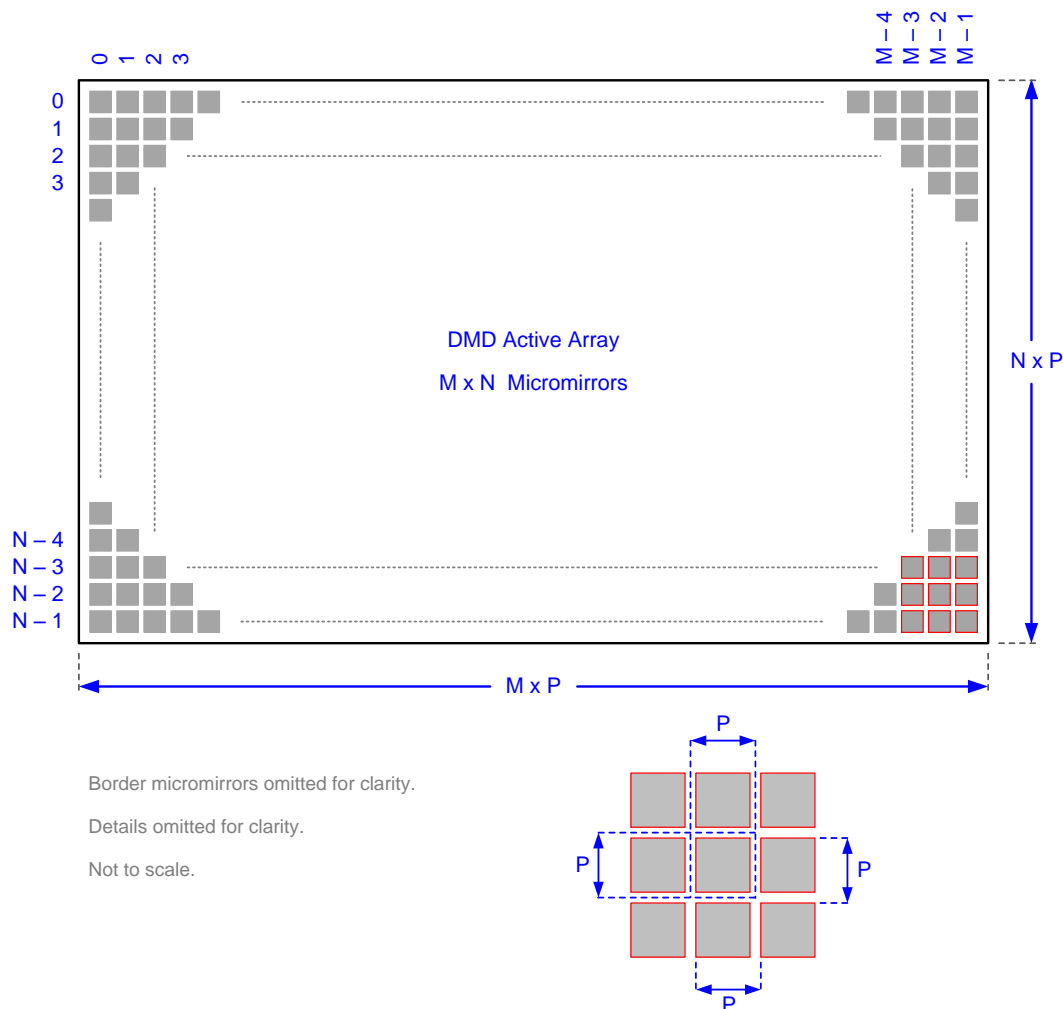
Figure 10. System Interface Loads

8.9 Micromirror Array Physical Characteristics

Additional details are provided in the [机械、封装和可订购信息](#) section at the end of this document.

PARAMETER				VALUE	UNIT
M	Number of active micromirror columns		See Micromirror Array Physical Characteristics	1024	micromirrors
N	Number of active micromirror rows			768	
P	Micromirror pitch			10.8	μm
	Micromirror active array width	$M \times P$		11.059	mm
	Micromirror active array height	$N \times P$		8.294	mm
	Micromirror active array border	Pond of Micromirror (POM) ⁽¹⁾		10	micromirrors /side

- (1) The structure and qualities of the border around the active array includes a band of partially functional micromirrors called the POM. These micromirrors are structurally and/or electrically prevented from tilting toward the bright or ON state, but still require an electrical bias to tilt toward OFF.



Refer to the [Micromirror Array Physical Characteristics](#) table for M, N, and P specifications.

Figure 11. Micromirror Array Physical Characteristics

8.10 Micromirror Array Optical Characteristics

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-off's between numerous component and system design parameters. See the Application Notes for additional details, considerations, and guidelines: *DLP System Optics Application Report (DLPA022)*.

PARAMETER	CONDITIONS	MIN	NOM	MAX	UNIT
Micromirror tilt angle, a	DMD parked state ⁽¹⁾⁽²⁾⁽³⁾ , see Figure 15		0		degrees
	DMD landed state ⁽¹⁾⁽⁴⁾⁽⁵⁾ , see Figure 15		12		
Micromirror tilt angle variation, b ⁽¹⁾⁽⁴⁾⁽⁶⁾⁽⁷⁾⁽⁸⁾	See Figure 15	-1		1	degrees
Micromirror Cross Over Time ⁽⁹⁾			16	22	μs
Micromirror Switching Time ⁽¹⁰⁾			140		μs
Non Operating micromirrors ⁽¹¹⁾	Non-adjacent micromirrors			10	micromirrors
	Adjacent micromirrors			0	
Orientation of the micromirror axis-of-rotation ⁽¹²⁾	See	44	45	46	degrees
Micromirror array optical efficiency ⁽¹³⁾⁽¹⁴⁾	420 - 700, with all micromirrors in the ON state		68%		nm
Mirror metal specular reflectivity	420 - 700		89.4%		nm

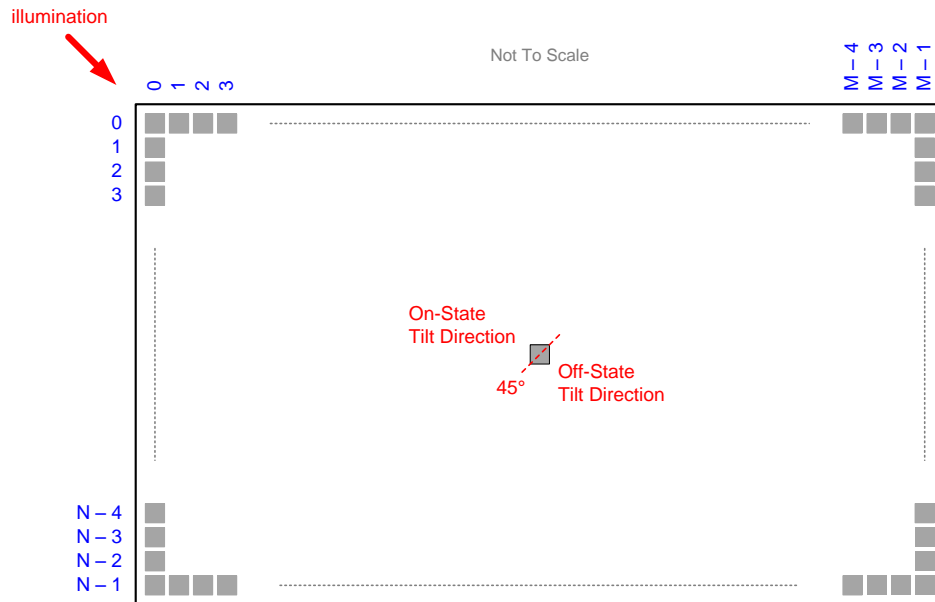
- (1) Measured relative to the plane formed by the overall micromirror array
- (2) Parking the micromirror array returns all of the micromirrors to an essentially flat (0°) state (as measured relative to the plane formed by the overall micromirror array).
- (3) When the micromirror array is parked, the tilt angle of each individual micromirror is uncontrolled.
- (4) Additional variation exists between the micromirror array and the package datums, as shown in the section at the end of the document.
- (5) When the micromirror array is landed, the tilt angle of each individual micromirror is dictated by the binary contents of the CMOS memory cell associated with each individual micromirror. A binary value of 1 will result in a micromirror landing in an nominal angular position of +12 degrees. A binary value of 0 will result in a micromirror landing in an nominal angular position of -12 degrees.
- (6) Represents the landed tilt angle variation relative to the Nominal landed tilt angle.
- (7) Represents the variation that can occur between any two individual micromirrors, located on the same device or located on different devices.
- (8) For some applications, it is critical to account for the micromirror tilt angle variation in the overall System Optical Design. With some System Optical Designs, the micromirror tilt angle variations within a device may result in perceivable non-uniformities in the light field reflected from the micromirror array. With some System Optical Designs, the micromirror tilt angle variation between devices may result in colorimetry variations and/or system contrast variations.
- (9) Micromirror Cross Over time is primarily a function of the natural response time of the micromirrors.
- (10) Micromirror switching is controlled and coordinated by the DLPC200 (See [DLPS014](#)) and DLP4200 (See [DLPS015](#)). Nominal Switching time depends on the system implementation and represents the time for the entire micromirror array to be refreshed.
- (11) Non-operating micromirror is defined as a micromirror that is unable to transition nominally from the -12 degree position to +12 degree or vice versa.
- (12) Measured relative to the package datums B and C, shown in the [机械、封装和可订购信息](#) section at the end of this document.
- (13) The minimum or maximum DMD optical efficiency observed in a specific application depends on numerous application-specific design variables, such as but not limited to:
 - (a) Illumination wavelength, bandwidth or line-width, degree of coherence
 - (b) Illumination angle, plus angle tolerance
 - (c) Illumination and projection aperture size, and location in the system optical path
 - (d) Illumination overfill of the DMD micromirror array
 - (e) Aberrations present in the illumination source and/or path
 - (f) Aberrations present in the projection path

The specified nominal DMD optical efficiency is based on the following use conditions:

 - (a) Visible illumination (420 nm – 700 nm)
 - (b) Input illumination optical axis oriented at 24° relative to the window normal
 - (c) Projection optical axis oriented at 0° relative to the window normal
 - (d) f/3.0 illumination aperture
 - (e) f/2.4 projection aperture

Based on these use conditions, the nominal DMD optical efficiency results from the following four components:

 - (a) Micromirror array fill factor: nominally 92%
 - (b) Micromirror array diffraction efficiency: nominally 86%
 - (c) Micromirror surface reflectivity: nominally 88%
 - (d) Window transmission: nominally 97% (single pass, through two surface transitions)
- (14) Does not account for the effect of micromirror switching duty cycle, which is application dependant. Micromirror switching duty cycle represents the percentage of time that the micromirror is actually reflecting light from the optical illumination path to the optical projection path. This duty cycle depends on the illumination aperture size, the projection aperture size, and the micromirror array update rate.



Refer to section [Micromirror Array Physical Characteristics](#) table for M, N, and P specifications.

Figure 12. Micromirror Landed Orientation and Tilt

8.11 Window Characteristics

PARAMETER ⁽¹⁾	CONDITIONS	MIN	TYP	MAX	UNIT
Window material designation	Corning Eagle XG				
Window refractive index	at wavelength 546.1 nm		1.5119		
Window aperture	See ⁽²⁾				
Illumination overfill	Refer to Illumination Overfill section				
Window transmittance, single-pass through both surfaces and glass ⁽³⁾	At wavelength 405 nm. Applies to 0° and 24° AOI only.	95%			
	Minimum within the wavelength range 420 nm to 680 nm. Applies to all angles 0° to 30° AOI.	97%			
	Average over the wavelength range 420 nm to 680 nm. Applies to all angles 30° to 45° AOI.	97%			

(1) See [Window Characteristics and Optics](#) for more information.

(2) For details regarding the size and location of the window aperture, see the package mechanical characteristics listed in the Mechanical ICD in the Mechanical, Packaging, and Orderable Information section.

(3) See the TI application report [Wavelength Transmittance Considerations for DLP® DMD Window DLP4031](#).

8.12 Chipset Component Usage Specification

The DLP5500 is a component of one or more DLP chipsets. Reliable function and operation of the DLP5500 requires that it be used in conjunction with the other components of the applicable DLP chipset, including those components that contain or implement TI DMD control technology. TI DMD control technology is the TI technology and devices for operating or controlling a DLP DMD.

9 Detailed Description

9.1 Overview

DLP5500 is a 0.55 inch diagonal spatial light modulator which consists of an array of highly reflective aluminum micromirrors. Pixel array size and square grid pixel arrangement are shown in [Figure 11](#).

The DMD is an electrical input, optical output micro-electrical-mechanical system (MEMS). The electrical interface is Low Voltage Differential Signaling (LVDS), Double Data Rate (DDR).

DLP5500 DMD consists of a two-dimensional array of 1-bit CMOS memory cells. The array is organized in a grid of M memory cell columns by N memory cell rows. Refer to the [Functional Block Diagram](#).

The positive or negative deflection angle of the micromirrors can be individually controlled by changing the address voltage of underlying CMOS addressing circuitry and micromirror reset signals (MBRST).

Each cell of the $M \times N$ memory array drives its true and complement ('Q' and 'QB') data to two electrodes underlying one micromirror, one electrode on each side of the diagonal axis of rotation. Refer to [Figure 15](#). The micromirrors are electrically tied to the micromirror reset signals (MBRST) and the micromirror array is divided into reset groups.

Electrostatic potentials between a micromirror and its memory data electrodes cause the micromirror to tilt toward the illumination source in a DLP projection system or away from it, thus reflecting its incident light into or out of an optical collection aperture. The positive (+) tilt angle state corresponds to an 'on' pixel, and the negative (–) tilt angle state corresponds to an 'off' pixel.

Refer to [Micromirror Array Optical Characteristics](#) for the \pm tilt angle specifications. Refer to the [Pin Configuration and Functions](#) for more information on micromirror clocking pulse (reset) control.

9.2 Functional Block Diagram

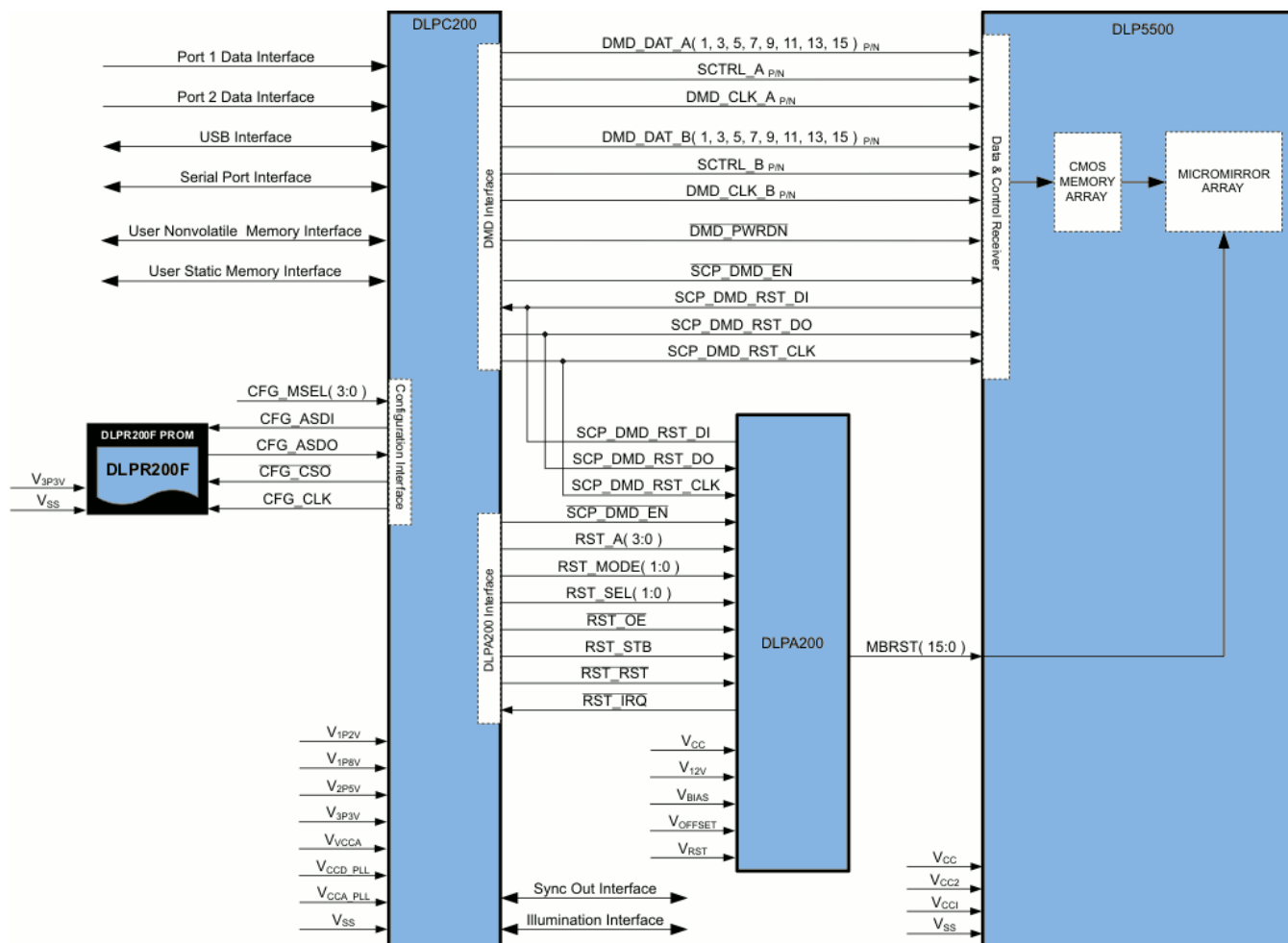


Figure 13. Functional Block Diagram

9.3 Feature Description

The DLP5500 device consists of 786,432 highly reflective, digitally switchable, micrometer-sized mirrors (micromirrors) organized in a two-dimensional orthogonal pixel array. Refer to [Figure 11](#) and [Figure 14](#).

Each aluminum micromirror is switchable between two discrete angular positions, $-a$ and $+a$. The angular positions are measured relative to the micromirror array plane, which is parallel to the silicon substrate. Refer to [Micromirror Array Optical Characteristics](#) and [Figure 15](#).

The parked position of the micromirror is not a latched position and is therefore not necessarily perfectly parallel to the array plane. Individual micromirror flat state angular positions may vary. Tilt direction of the micromirror is perpendicular to the hinge-axis. The on-state landed position is directed toward the left-top edge of the package, as shown in [Figure 14](#).

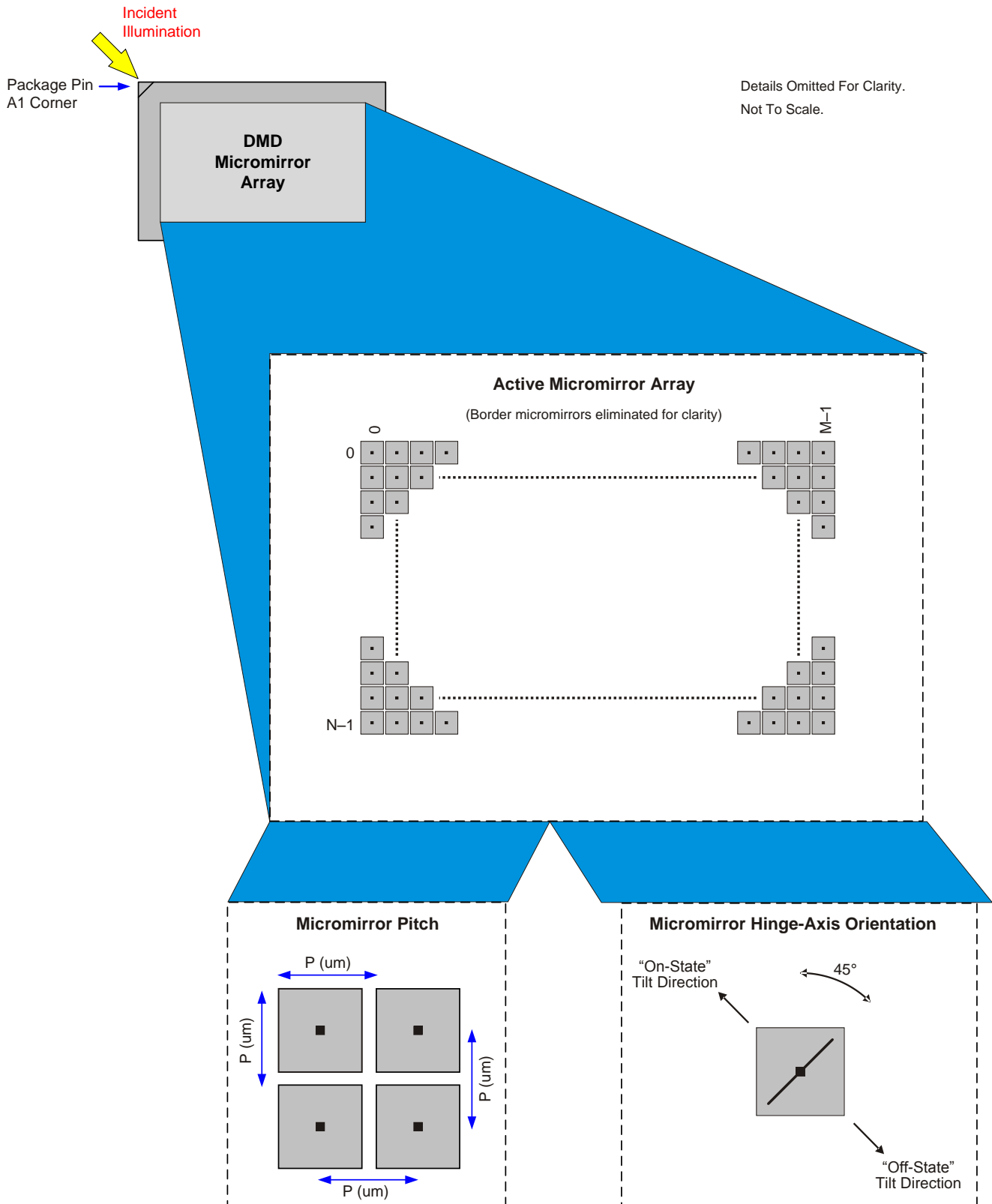
Each individual micromirror is positioned over a corresponding CMOS memory cell. The angular position of a specific micromirror is determined by the binary state (logic 0 or 1) of the corresponding CMOS memory cell contents, after the mirror clocking pulse is applied. The angular position ($-a$ and $+a$) of the individual micromirrors changes synchronously with a micromirror clocking pulse, rather than being coincident with the CMOS memory cell data update.

Writing logic 1 into a memory cell followed by a mirror clocking pulse results in the corresponding micromirror switching to the $+a$ position. Writing logic 0 into a memory cell followed by a mirror clocking pulse results in the corresponding micromirror switching to the $-a$ position.

Updating the angular position of the micromirror array consists of two steps. First, update the contents of the CMOS memory. Second, apply a micromirror clocking pulse (reset) to all or a portion of the micromirror array (depending upon the configuration of the system). Micromirror reset pulses are generated externally by the DLPC200 controller in conjunction with the DLPA200 analog driver, with application of the pulses being coordinated by the DLPC200 controller.

For more information, see the TI application report [DLPA008](#), *DMD101: Introduction to Digital Micromirror Device (DMD) Technology*.

Feature Description (continued)

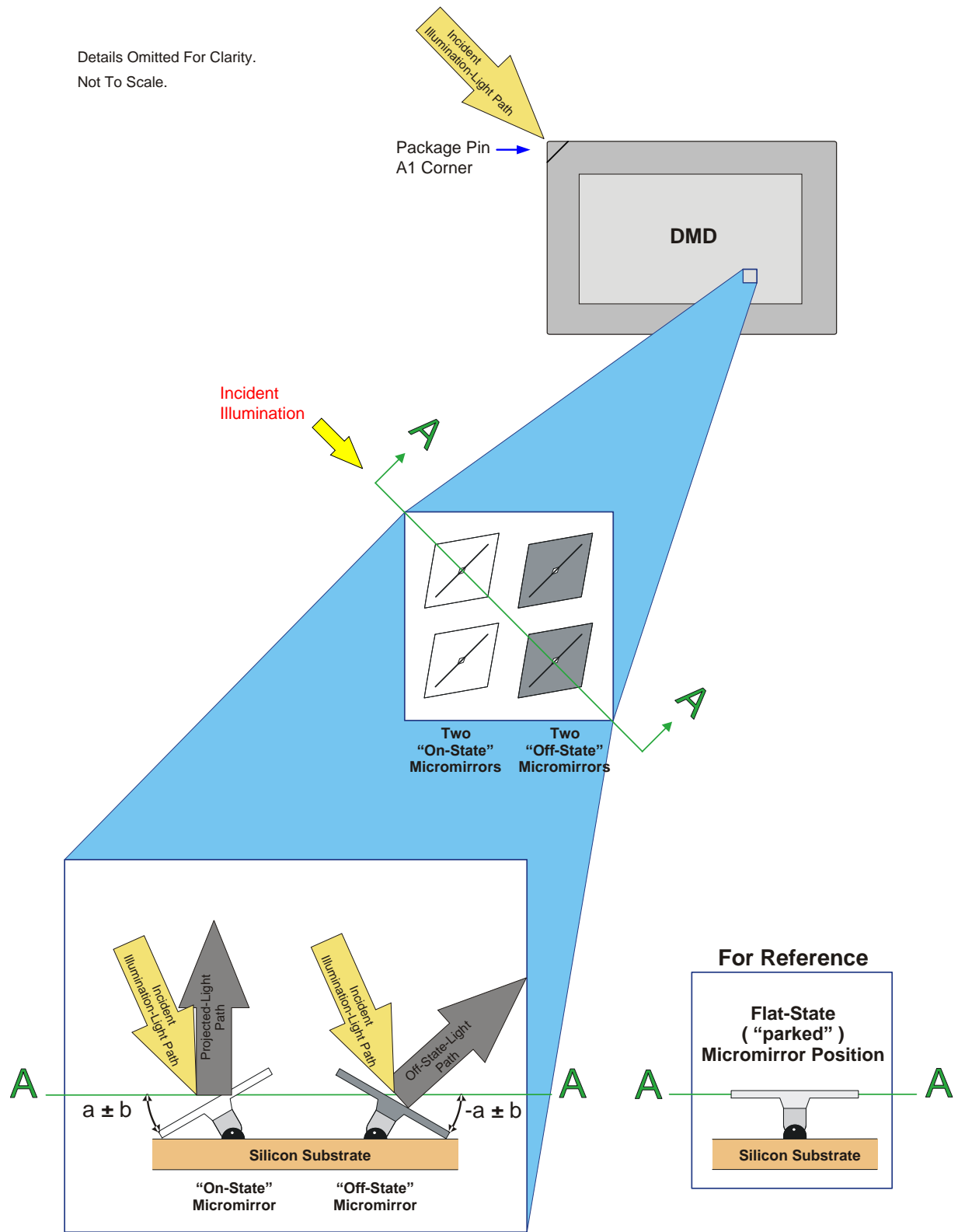


Refer to [Figure 11](#) and [Figure 12](#).

Figure 14. Micromirror Array, Pitch, Hinge Axis Orientation

Feature Description (continued)

Details Omitted For Clarity.
Not To Scale.



Micromirror States: On, Off, Flat

Figure 15. Micromirror States: On, Off, Flat

9.4 Device Functional Modes

DMD functional modes are controlled by the DLPC200 digital display controller. See the [DLPC200](#) data sheet listed in [相关文档](#). Contact a TI applications engineer for more information.

The DLPC200 provides two basic functional mode types to control the DLP5500 DMD: video and structured light.

9.4.1 Video Modes

The controller accepts RGB-8-8-8 input to port 1 or port 2 through a selectable MUX. XGA video information is displayed on the DMD at 6 to 60 fps.

An internal pattern generator can generate RGB-8-8-8 video patterns into an internal selectable MUX for verification and debug purposes.

9.4.2 Structured Light Modes

The DLPC200 provides two structured light modes: static image buffer and real-time structured light.

9.4.2.1 Static Image Buffer Mode

Image data can be loaded into parallel flash memory to load to DDR2 memory at startup to be displayed, or can be loaded over USB or the SPI port directly to DDR2 memory to be displayed. Binary (1-bit) or grayscale (8-bit) patterns can be displayed. The memory will hold 960 binary patterns or 120 grayscale patterns.

Binary (1-bit) patterns can be displayed at up to 5000 binary patterns per second. These patterns assume a constant illumination and do not depend on illumination modulation.

Grayscale (8-bit) patterns assume illumination modulation in order to achieve higher pattern rates. When the pattern rate requires that the lower significant bit(s) be shorter than the rate that the DMD can be switched, these bits will require the source to be modulated to achieve the shorter time required. The trade-off is dark time during these bits. At the maximum 500 Hz grayscale pattern rate, the dark time approaches 75%.

9.4.2.2 Real Time Structured Light Mode

RGB-8-8-8 60 fps data can be input into port 1 or port 2 and reinterpreted as up to 24 binary (1-bit) patterns or three grayscale (8-bit) patterns. The specified number of patterns is displayed equally during the exposure time specified. Any unused RGB-8-8-8 data in the video frame must be filled with data, usually 0s.

For example, during one video frame (16.67 ms), 12 binary patterns of the 24 RGB bits are requested to be displayed during half of the video frame time (exposure time = 8.33 ms). Each of the eight red bits and the four most significant green bits are displayed as a binary pattern for 694 μ s each. The remaining bits are ignored and the remaining 8.33 ms of the frame will be dark.

9.5 Window Characteristics and Optics

NOTE

TI assumes no responsibility for image quality artifacts or DMD failures caused by optical system operating conditions exceeding limits described previously.

9.5.1 Optical Interface and System Image Quality

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-offs between numerous component and system design parameters. Optimizing system optical performance and image quality strongly relate to optical system design parameter trades. Although it is not possible to anticipate every conceivable application, projector image quality and optical performance is contingent on compliance to the optical system operating conditions described in the following sections.

Window Characteristics and Optics (continued)

9.5.2 Numerical Aperture and Stray Light Control

The angle defined by the numerical aperture of the illumination and projection optics at the DMD optical area should be the same. This angle should not exceed the nominal device mirror tilt angle unless appropriate apertures are added in the illumination and/or projection pupils to block out flat-state and stray light from the projection lens. The mirror tilt angle defines DMD capability to separate the "ON" optical path from any other light path, including undesirable flat-state specular reflections from the DMD window, DMD border structures, or other system surfaces near the DMD such as prism or lens surfaces. If the numerical aperture exceeds the mirror tilt angle, or if the projection numerical aperture angle is more than two degrees larger than the illumination numerical aperture angle, objectionable artifacts in the display's border and/or active area could occur.

9.5.3 Pupil Match

TI's optical and image quality specifications assume that the exit pupil of the illumination optics is nominally centered within 2° (two degrees) of the entrance pupil of the projection optics. Misalignment of pupils can create objectionable artifacts in the display's border and/or active area, which may require additional system apertures to control, especially if the numerical aperture of the system exceeds the pixel tilt angle.

9.5.4 Illumination Overfill

The active area of the device is surrounded by an aperture on the inside DMD window surface that masks structures of the DMD device assembly from normal view. The aperture is sized to anticipate several optical operating conditions. Overfill light illuminating the window aperture can create artifacts from the edge of the window aperture opening and other surface anomalies that may be visible on the screen. The illumination optical system should be designed to limit light flux incident anywhere on the window aperture from exceeding approximately 10% of the average flux level in the active area. Depending on the particular system's optical architecture, overfill light may have to be further reduced below the suggested 10% level in order to be acceptable.

9.6 Micromirror Array Temperature Calculation

Achieving optimal DMD performance requires proper management of the maximum DMD case temperature, the maximum temperature of any individual micromirror in the active array, the maximum temperature of the window aperture, and the temperature gradient between case temperature and the predicted micromirror array temperature. (see [Figure 16](#)).

Refer to the [Recommended Operating Conditions](#) for applicable temperature limits.

9.6.1 Package Thermal Resistance

The DMD is designed to conduct absorbed and dissipated heat to the back of the Series 450 package where it can be removed by an appropriate heat sink. The heat sink and cooling system must be capable of maintaining the package within the specified operational temperatures, refer to [Figure 16](#). The total heat load on the DMD is typically driven by the incident light absorbed by the active area; although other contributions include light energy absorbed by the window aperture and electrical power dissipation of the array.

9.6.2 Case Temperature

The temperature of the DMD case can be measured directly. For consistency, Thermal Test Point locations TP1 - TP5 are defined, as shown in [Figure 16](#).

Micromirror Array Temperature Calculation (continued)

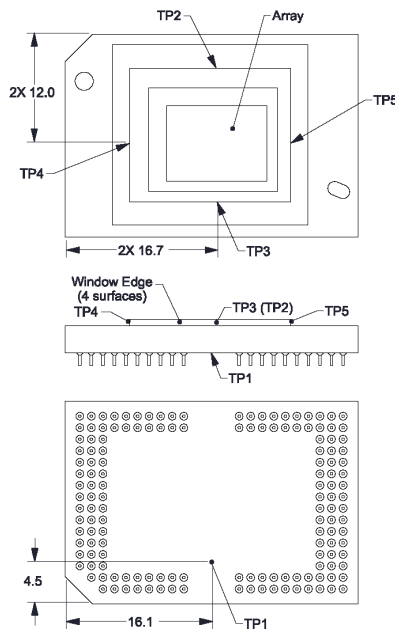


Figure 16. Thermal Test Point Location

9.6.3 Micromirror Array Temperature Calculation for Uniform Illumination

Micromirror array temperature cannot be measured directly; therefore it must be computed analytically from measurement points (Figure 16), the package thermal resistance, the electrical power, and the illumination heat load. The relationship between micromirror array temperature and the case temperature are provided by Equation 1 and Equation 2:

$$T_{\text{Array}} = T_{\text{Ceramic}} + (Q_{\text{Array}} \times R_{\text{Array-To-Ceramic}}) \quad (1)$$

$$Q_{\text{Array}} = Q_{\text{ELE}} + Q_{\text{ILL}}$$

Where the following elements are defined as:

- T_{Array} = computed micromirror array temperature (°C)
- T_{Ceramic} = Ceramic temperature (°C) (TC2 Location Figure 16)
- Q_{Array} = Total DMD array power (electrical + absorbed) (measured in Watts)
- $R_{\text{Array-To-Ceramic}}$ = thermal resistance of DMD package from array to TC2 (°C/Watt) (see [Package Thermal Resistance](#))
- Q_{ELE} = Nominal electrical power (Watts)
- Q_{ILL} = Absorbed illumination energy (Watts) (2)

An example calculation is provided below based on a traditional DLP Video projection system. The electrical power dissipation of the DMD is variable and depends on the voltages, data rates, and operating frequencies. The nominal electrical power dissipation to be used in the calculation is 2.0 Watts. Thus, $Q_{\text{ELE}} = 2.0$ Watts. The absorbed power from the illumination source is variable and depends on the operating state of the mirrors and the intensity of the light source. It's based on modeling and measured data from DLP projection system.

$$Q_{\text{ILL}} = C_{\text{L2W}} \times \text{SL}$$

Where:

- C_{L2W} is a Lumens to Watts constant, and can be estimated at 0.00274 Watt/Lumen
- SL = Screen Lumens nominally measured to be 2000 lumens
- $Q_{\text{array}} = 2.0 + (0.00274 \times 2000) = 7.48$ watts, Estimated total power on micromirror Array
- $T_{\text{Ceramic}} = 55^\circ\text{C}$, assumed system measurement
- T_{Array} (micromirror active array temperature) = $55^\circ\text{C} + (7.48 \text{ watts} \times 0.6^\circ\text{C/watt}) = 59.5^\circ\text{C}$ (3)

Micromirror Array Temperature Calculation (continued)

For additional explanation of DMD Mechanical and Thermal calculations and considerations please refer to *DLP Series-450 DMD and System Mounting Concepts* (DLPA015).

9.7 Micromirror Landed-on/Landed-Off Duty Cycle

9.7.1 Definition of Micromirror Landed-On/Landed-Off Duty Cycle

The micromirror landed-on/landed-off duty cycle (landed duty cycle) denotes the amount of time (as a percentage) that an individual micromirror is landed in the On-state versus the amount of time the same micromirror is landed in the Off-state.

As an example, a landed duty cycle of 100/0 indicates that the referenced pixel is in the On-state 100% of the time (and in the Off-state 0% of the time); whereas 0/100 would indicate that the pixel is in the Off-state 100% of the time. Likewise, 50/50 indicates that the pixel is On 50% of the time and Off 50% of the time.

Note that when assessing landed duty cycle, the time spent switching from one state (ON or OFF) to the other state (OFF or ON) is considered negligible and is thus ignored.

Since a micromirror can only be landed in one state or the other (On or Off), the two numbers (percentages) always add to 100.

9.7.2 Landed Duty Cycle and Useful Life of the DMD

Knowing the long-term average landed duty cycle (of the end product or application) is important because subjecting all (or a portion) of the DMD's micromirror array (also called the active array) to an asymmetric landed duty cycle for a prolonged period of time can reduce the DMD's usable life.

Note that it is the symmetry/asymmetry of the landed duty cycle that is of relevance. The symmetry of the landed duty cycle is determined by how close the two numbers (percentages) are to being equal. For example, a landed duty cycle of 50/50 is perfectly symmetrical whereas a landed duty cycle of 100/0 or 0/100 is perfectly asymmetrical.

9.7.3 Landed Duty Cycle and Operational DMD Temperature

Operational DMD Temperature and Landed Duty Cycle interact to affect the DMD's usable life, and this interaction can be exploited to reduce the impact that an asymmetrical Landed Duty Cycle has on the DMD's usable life. This is quantified in the de-rating curve shown in [Figure 1](#). The importance of this curve is that:

- All points along this curve represent the same usable life.
- All points above this curve represent lower usable life (and the further away from the curve, the lower the usable life).
- All points below this curve represent higher usable life (and the further away from the curve, the higher the usable life).

In practice, this curve specifies the Maximum Operating DMD Temperature that the DMD should be operated at for a give long-term average Landed Duty Cycle.

9.7.4 Estimating the Long-Term Average Landed Duty Cycle of a Product or Application

During a given period of time, the Landed Duty Cycle of a given pixel follows from the image content being displayed by that pixel.

For example, in the simplest case, when displaying pure-white on a given pixel for a given time period, that pixel will experience a 100/0 Landed Duty Cycle during that time period. Likewise, when displaying pure-black, the pixel will experience a 0/100 Landed Duty Cycle.

Between the two extremes (ignoring for the moment color and any image processing that may be applied to an incoming image), the Landed Duty Cycle tracks one-to-one with the gray scale value, as shown in [Table 1](#).

Table 1. Grayscale Value and Landed Duty Cycle

GRAYSCALE VALUE	LANDED DUTY CYCLE
0%	0/100
10%	10/90
20%	20/80
30%	30/70
40%	40/60
50%	50/50
60%	60/40
70%	70/30
80%	80/20
90%	90/10
100%	100/0

Accounting for color rendition (but still ignoring image processing) requires knowing both the color intensity (from 0% to 100%) for each constituent primary color (red, green, and/or blue) for the given pixel as well as the color cycle time for each primary color, where “color cycle time” is the total percentage of the frame time that a given primary must be displayed in order to achieve the desired white point.

During a given period of time, the landed duty cycle of a given pixel can be calculated as follows:

$$\text{Landed Duty Cycle} = (\text{Red_Cycle_}\% \times \text{Red_Scale_Value}) + (\text{Green_Cycle_}\% \times \text{Green_Scale_Value}) + (\text{Blue_Cycle_}\% \times \text{Blue_Scale_Value})$$

where

- Red_Cycle_%, Green_Cycle_%, and Blue_Cycle_%, represent the percentage of the frame time that Red, Green, and Blue are displayed (respectively) to achieve the desired white point. (4)

For example, assume that the red, green and blue color cycle times are 50%, 20%, and 30% respectively (in order to achieve the desired white point), then the Landed Duty Cycle for various combinations of red, green, blue color intensities would be as shown in [Table 2](#).

Table 2. Example Landed Duty Cycle for Full-Color

Red Cycle Percentage 50%	Green Cycle Percentage 20%	Blue Cycle Percentage 30%	Landed Duty Cycle
Red Scale Value	Green Scale Value	Blue Scale Value	
0%	0%	0%	0/100
100%	0%	0%	50/50
0%	100%	0%	20/80
0%	0%	100%	30/70
12%	0%	0%	6/94
0%	35%	0%	7/93
0%	0%	60%	18/82
100%	100%	0%	70/30
0%	100%	100%	50/50
100%	0%	100%	80/20
12%	35%	0%	13/87
0%	35%	60%	25/75
12%	0%	60%	24/76
100%	100%	100%	100/0

10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The DLP5500 (0.55-inch XGA DMD) is controlled by the DLPC200 controller in conjunction with the DLPA200 driver. This combination can be used for a number of applications from 3D printers to microscopes.

The most common application is for 3D structured light measurement applications. In this application, patterns (binary, grayscale, or even full color) are projected onto the target and the distortion of the patterns are recorded by an imaging device to extract 3D (x, y, z) surface information.

10.2 Typical Application

A schematic is shown in Figure 17 for projecting RGB and IR structured light patterns onto a measurement target. Typically, an imaging device is triggered through one of the three syncs to record the data as each pattern is displayed.

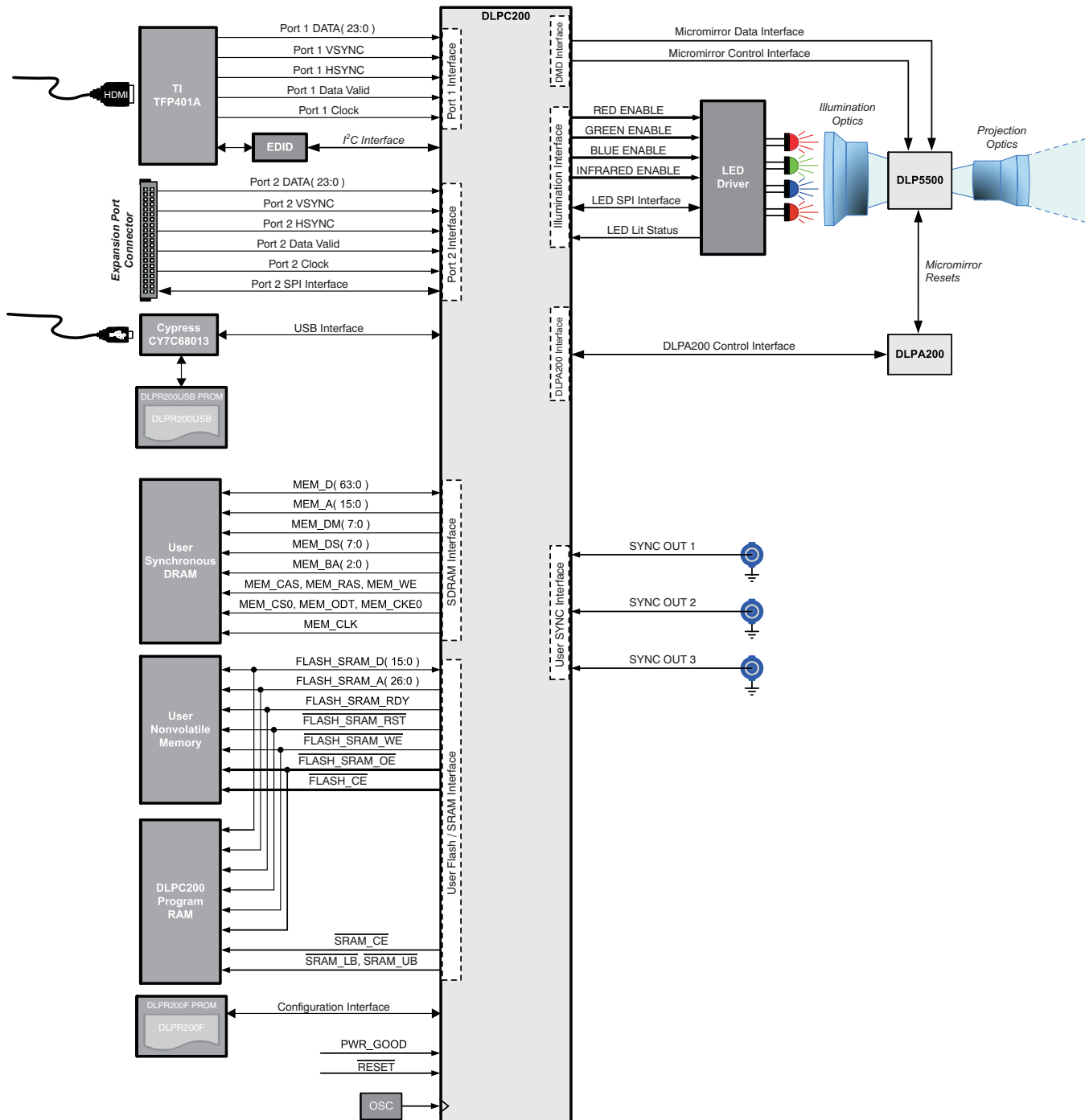


Figure 17. Typical RGB + IR Structured Light Application

Typical Application (continued)

10.2.1 Design Requirements

All applications using the DLP 0.55-inch XGA chipset require the DLPC200 controller, the DLPA200 driver, and the DLP5500 DMD for correct operation. The system also requires user supplied SRAM and a configuration PROM programmed with the DLPR200F program file and a 50-MHz oscillator is for operation. For further details, refer to the DLPC200 controller data sheet ([DLPS014](#)) and the DLPA200 analog driver data sheet ([DLPS015](#)).

10.2.2 Detailed Design Procedure

10.2.2.1 DLP5500 System Interface

Images are displayed on the DLP5500 via the DLPC200 controller and the DLPA200 driver. The DLP5500 interface consists of a 200-MHz (nominal) half-bus DDR input-only interface with LVDS signaling. The serial communications port (SCP), 125-kHz nominal, is used by the DLPC200 to read or write control data to both the DLP5500 and the DLPA200. The following listed signals support data transfer to the DLP5500 and DLPA200.

- DMD, 200 MHz
 - DMD_CLK_AP, DMD_CLK_AN – DMD clock for A
 - DMD_CLK_BP, DMD_CLK_BN – DMD clock for B
 - DMD_DAT_AP, DMD_DAT_AN(1, 3, 5, 7, 9, 11, 13, 15) – Data bus A (odd-numbered pins are used for half-bus)
 - DMD_DAT_BP, DMD_DAT_BN(1, 3, 5, 7, 9, 11, 13, 15) – Data bus B (odd-numbered pins are used for half-bus)
 - DMD_SCRTL_AP, DMD_SCRTL_AN – S-control for A
 - DMD_SCRTL_BP, DMD_SCRTL_BN – S-control for B
- DLPA200, 125 kHz
 - SCP_DMD_RST_CLK – SCP clock
 - SCP_DMD_EN – Enable DMD communication
 - SCP_RST_EN – Enable DLPA200 communication
 - SCP_DMD_RST_DI – Input data
 - SCP_DMD_RST_DO – Output data

11 Power Supply Recommendations

11.1 DMD Power-Up and Power-Down Procedures

The DLP5500 power-up and power-down procedures are defined by the DLPC200 data sheet ([DLPS012](#)) and the *0.55 XGA Chipset* data sheet ([DLPZ004](#)). These procedures must be followed to ensure reliable operation of the device.

CAUTION

Failure to adhere to the prescribed power-up and power-down procedures may affect device reliability.

12 Layout

12.1 Layout Guidelines

The DLP5500 is part of a chipset that is controlled by the DLPC200 in conjunction with the DLPA200. These guidelines are targeted at designing a PCB board with these components.

12.1.1 Impedance Requirements

Signals should be routed to have a matched impedance of $50\ \Omega \pm 10\%$ except for LVDS differential pairs (DMD_DAT_Xnn, DMD_DCKL_Xn, and DMD_SCTRL_Xn) and DDR2 differential clock pairs (MEM_CLK_nn), which should be matched to $100\ \Omega \pm 10\%$ across each pair.

12.1.2 PCB Signal Routing

When designing a PCB board for the DLP5500 controlled by the DLPC200 in conjunction with the DLPA200, the following are recommended:

Signal trace corners should be no sharper than 45° . Adjacent signal layers should have the predominate traces routed orthogonal to each other. TI recommends that critical signals be hand routed in the following order: DDR2 Memory, DMD (LVDS signals), then DLPA200 signals.

TI does not recommend signal routing on power or ground planes.

TI does not recommend ground plane slots.

High speed signal traces should not cross over slots in adjacent power and/or ground planes.

Table 3. LVDS Trace Constraints

Signal	Constraints
LVDS (DMD_DAT_xnn, DMD_DCKL_xn, and DMD_SCTRL_xn)	P-to-N data, clock, and SCTRL: <10 mils (0.25 mm); Pair-to-pair <10 mils (0.25 mm); Bundle-to-bundle <2000 mils (50 mm, for example DMD_DAT_Ann to DMD_DAT_Bnn). All matching should include internal trace lengths. See Pin Configuration and Functions for internal package trace lengths. Trace width: 4 mil (0.1 mm) Trace spacing: In ball field – 4 mil (0.11 mm); PCB etch – 14 mil (0.36 mm) Maximum recommended trace length <6 inches (150 mm)

Table 4. Power and Mirror Clocking Pulse Trace Widths and Spacing

Signal Name	Minimum Trace Width	Minimum Trace Spacing	Layout Requirements
GND	Maximize	5 mil (0.13 mm)	Maximize trace width to connecting pin as a minimum
VCC, VCC2	20 mil (0.51 mm)	10 mil (0.25 mm)	
MBRST[15:0]	10 mil (0.25 mm)	10 mil (0.25 mm)	

12.1.3 Fiducials

Fiducials for automatic component insertion should be 0.05-inch copper with a 0.1-inch cutout (antipad). Fiducials for optical auto insertion are placed on three corners of both sides of the PCB.

12.2 Layout Example

For LVDS (and other differential signal) pairs and groups, it is important to match trace lengths. In the area of the dashed lines, [Figure 18](#) shows correct matching of signal pair lengths with serpentine sections to maintain the correct impedance.

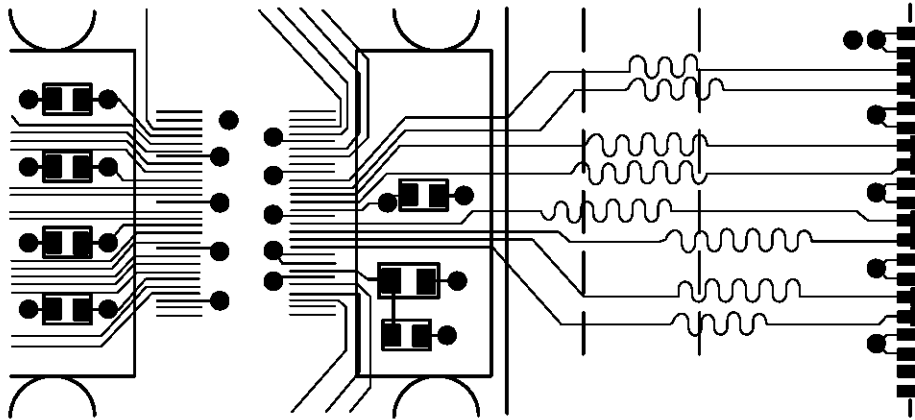


Figure 18. Mitering LVDS Traces to Match Lengths

13 器件和文档支持

13.1 器件支持

13.1.1 器件命名规则

器件标记由 图 19 中显示的字段组成。

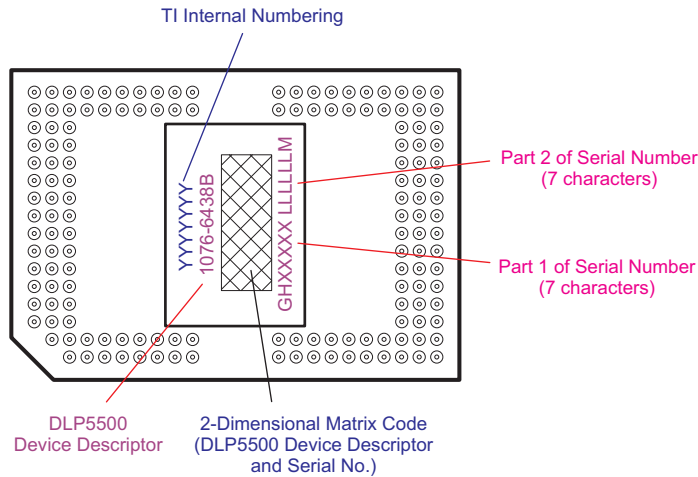


图 19. DMD 标记（器件顶视图）

13.2 文档支持

13.2.1 相关文档

以下文档包含关于使用 DLP5500 器件的更多信息：

- 《DLP 0.55 XGA 芯片组数据表》 [DLPZ004](#)
- 《DLPC200 数字控制器数据表》 [DLPS014](#)
- 《DLPA200 DMD 模拟复位驱动器》 [DLPS015](#)
- 《DLP 450 系列 DMD 和系统安装概念》 [DLPA015](#)
- 《DLPC200 API 参考手册》 [DLPA024](#)
- 《DLPC200 API 编程人员指南》 [DLPA014](#)
- 《s4xx DMD 清洁应用手册》 [DLPA025](#)
- 《s4xx DMD 处理应用手册》 [DLPA019](#)

13.3 相关文档

下表列出了快速访问链接。类别包括技术文档、支持与社区资源、工具和软件，以及申请样片或购买产品的快速链接。

相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持和社区
DLPA200	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
DLPC200	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

13.4 社区资源

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社区资源 (接下页)

设计支持 *TI 参考设计支持* 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

13.5 商标

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13.6 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

13.7 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

14 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DLP5500BFYA	ACTIVE	CPGA	FYA	149	5	RoHS & Green	NI-PD-AU	N / A for Pkg Type			Samples
DLPA200PFP	ACTIVE	HTQFP	PFP	80	5	TBD	Call TI	Call TI			Samples
DLPC200ZEW	ACTIVE	BGA	ZEW	780	5	TBD	Call TI	Call TI			Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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